Transys Electronics LIMITED

SOT-523 Plastic-Encapsulated Diodes

BAS16T/BAW56T/BAV70T/BAV99T

SWITCHING DIODE

SOT-523



FEATURES

Power dissipation

$P_{D:}$ 150 mW (Tamb=25℃)

Forward Current

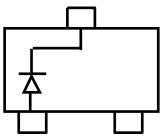
$I_{F:}$ 75 m A

Reverse Voltage

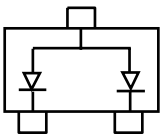
V_R: 85 V

Operating and storage junction temperature range

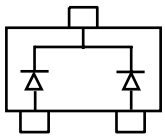
T_J, T_{stg}: -55℃ to +150℃



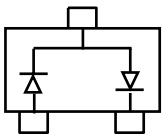
BAS16T Marking: A2



BAW56T Marking: JD



BAV70T Marking: JJ



BAV99T Marking: JE

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	I_R= 100μA	85		V
Reverse voltage leakage current	I_{R1}	V_R=75V		2	μA
	I_{R2}	V_R=25V		0.03	μA
Forward voltage	V_F	I_F=1mA I_F=10mA I_F=50mA I_F=150mA		715 855 1000 1250	mV
Diode capacitance	C_D	V_R=0V, f=1MHz		1.5	pF
Reverse recovery time	t_{rr}			4	nS

Typical Characteristics BAS16T/BAW56T/BAV70T/BAV99T

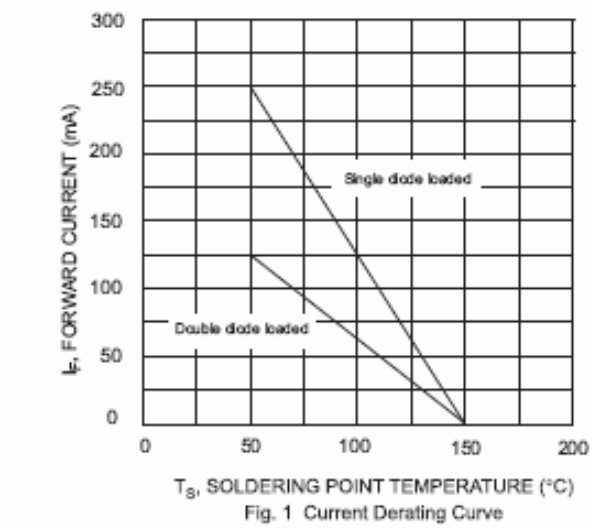


Fig. 1 Current Derating Curve

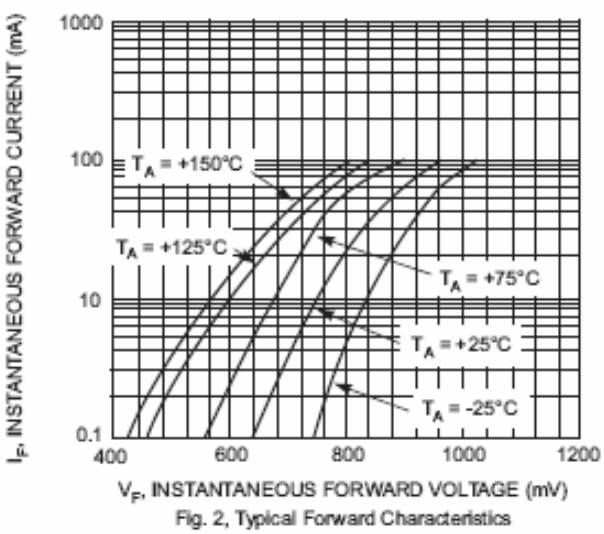


Fig. 2, Typical Forward Characteristics

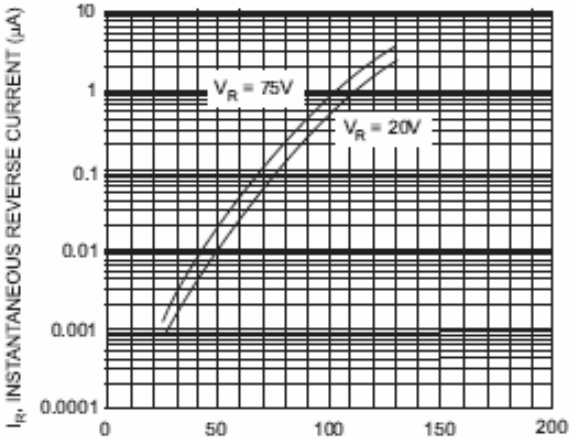


Fig. 3, Typical Reverse Characteristics